



## YES-CV200RFL Plasma Strip/Descum System

Powerful Cleaning Removes Photoresist, Polyimide and BCB;  
With Gentle Descum Function

### Specifications

|                              |   |
|------------------------------|---|
| <b>Hardware</b>              |   |
| Clean Room Compatibility     | Class 10  |
| Wafer Temperature Range      | Ambient to 300 °C   |
| Capacity                     | Single wafer/pieces for 50mm - 200mm                                    |
| Process Gas Inputs           | 4 standard  |
| Mass Flow Controllers        | Optional, up to 4 for gas mixing  |
| Interior Chamber Dimensions  | 25.4 cm (W) x 28.575 cm (D) x 4.978 cm (H)<br>(10" x 11.25" x 1.96")    |
| Hot Plate Process Area       | 49 in <sup>2</sup> maximum (200mm wafer)                                |
| Overall System Dimensions    | 50.8 cm (W) x 144.78(D) x 190.5 cm (H)<br>(20" x 57" x 75")             |
| Chamber Material             | 6061-T6 aluminum  |
| Compliance                   | SEMI S2, CE, S8   |
| <b>Software</b>              |   |
| PC                           | Monitor with pull out keyboard and automation control                   |
| Number of Recipes            | 12 with load/save/loop/link capability                                  |
| Data Collection              | YES-DAQ standard, SECS/GEM required                                     |
| <b>Performance</b>           |   |
| Power                        | 200-250 VAC, 40 amps (estimated)  |
| <b>Descum Specifications</b> |   |
| • Handling Speed             | 30 sec/wafer  |
| • Min. Process Time and Temp | 10-30 seconds   |
| • Minimum Etch Rate          | 200Å /min   |
| • Uniformity (Gallium)       | Within Wafer: +/- 4%<br>Wafer to Wafer: +/- 5%<br>Lot to Lot: +/- 5%    |
| • Uniformity (Silicon)       | Within Wafer: +/- 4%<br>Wafer to Wafer: +/- 5%<br>Lot to Lot: +/- 5%    |
| <b>Etch Specifications</b>   |   |
| • Minimum Process Time       | 30 Seconds - 2 minutes, assuming 20000 Å photoresist                    |
| • Minimum Etch Rate          | 7000Å/min @ 200°C, higher at 300°C                                      |
| • Uniformity                 | Within Wafer: +/- 10%<br>Wafer to Wafer: +/- 10%<br>Lot to Lot: +/- 10% |
| <b>Additional</b>            |   |
| Power Requirements           | 200-250V, 20 amps, 50/60 Hz, 1 phase                                    |
| Power Supply                 | Automatic frequency tuning  |



### Contact Us

When you're ready to run process tests, a demonstration can be arranged using your chemicals and samples. Call +46 8 319000 or visit us at [www.bitase.se](http://www.bitase.se)

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